# PUB4120 (PU4120), PUB4420 (PU4420)

### Silicon NPN triple diffusion planar type darlington

#### For power amplification

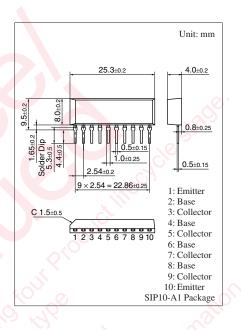
Complementary to PUB4220 (PU4220), PUB4520 (PU4520)

#### Features

- $\bullet$  High forward current transfer ratio  $h_{FE}$
- High-speed switching
- PUB4120 (PU4120): NPN 4 elements PUB4420 (PU4420): NPN 2 elements × 2

#### Absolute Maximum Ratings $T_C = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	60	V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	5	V
Collector current	I <sub>C</sub>	4	A
Peak collector current	I <sub>CP</sub>	8	А
Collector power dissipation	P <sub>C</sub>	15	W
$T_a = 25^{\circ}C$		3.5	
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C



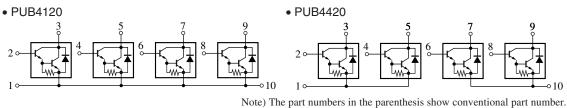
#### Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

			N			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 0$	60	×0		V
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = 3 V, I_C = 3 A$	JY.	V.	2.5	V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 60 \text{ V}, I_E = 0$			200	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 30 \text{ V}, I_B = 0$		15	500	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 5 V, I_C = 0$	2 ·	~	2	mA
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 3 V, I_C = 0.5 A$	1 000			_
	h <sub>FE2</sub> *	$V_{CE} = 3 V, I_C = 3 A$	1 000		10000	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 3 \text{ A}, I_{\rm B} = 12 \text{ mA}$	2		2.0	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 10 \text{ V}, I_C = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t <sub>on</sub>	$I_C = 3 A$		0.5		μs
Storage time	t <sub>stg</sub>	$I_{B1} = 12 \text{ mA}, I_{B2} = -12 \text{ mA}$		4.0		μs
Fall time	t <sub>f</sub>	$V_{CC} = 50 V$		1.0		μs

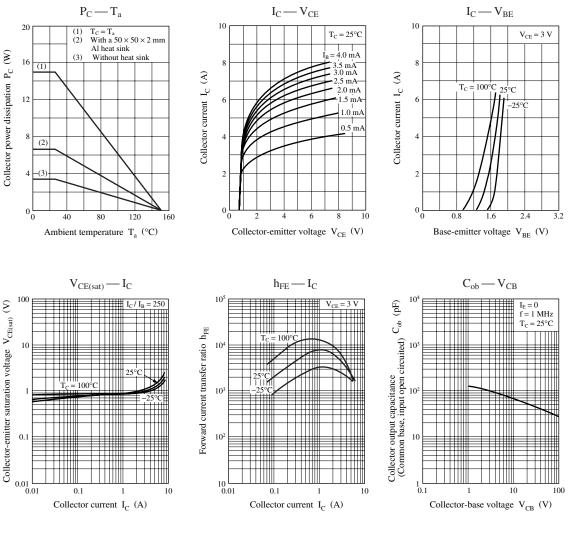
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. \*: Rank classification

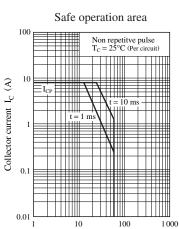
Rank	Free	PS	Q
$h_{FE}$	1000 to $10000$	2000 to 10000	1000 to 5000

#### Internal Connection



### Panasonic





Collector-emitter voltage V<sub>CE</sub> (V)

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